

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A thin film transistor type display device, comprising:

a first substrate;

a second substrate;

thin film transistors formed on the first substrate;

wiring lines formed on the second substrate; and

an element chip including at least one of the thin film transistors peeled off from the first substrate and transferred to the second substrate, holographic lithography being used in patterning of the thin film transistors.

2. (Original) A thin film transistor type display device, comprising:

a first substrate;

a second substrate;

thin film transistors formed on the first substrate;

wiring lines formed on the second substrate; and

an element chip including at least one of the thin film transistors peeled off from the first substrate and transferred to the second substrate, dynamic auto focus system being used in patterning of the thin film transistors.

3. (Original) The thin film transistor type display device according to Claim 1,

a design rule of 1.0 μm or less being used in the patterning of the thin film

transistors.

4. (Original) The thin film transistor type display device according to Claim 1,

only a polycrystalline silicon layer and a first metal layer being used as the

wiring lines of the element chip.

5. (Currently Amended) A method of manufacturing thin film elements, comprising:

transferring functional elements formed on a first substrate to a second substrate;

forming the functional elements in a predetermined shape on the first substrate via a peeling layer which causes peeling by the application of a predetermined amount of energy; and

transferring at least one of the functional elements to the second substrate by applying the energy to relevant portions of the peeling layer corresponding to the regions of the functional elements to cause peeling;

the-forming the functional elements in a predetermined shape including using holographic lithography to pattern the functional elements.

6. (Original) The method of manufacturing thin film elements according to Claim 5,

the functional elements being thin film transistors.

7. (Original) A thin film transistor circuit board, comprising:

thin film transistors manufactured by the method of manufacturing the thin film elements according to Claim 6.

8. (Original) An electro-optical device, comprising:

the thin film transistor circuit board according to Claim 7.

9. (Original) An electronic apparatus, comprising:

the electro-optical device according to Claim 8.

10. (New) The method of manufacturing thin film elements according to Claim 5, further comprising:

using a design rule of 1.0 μm or less to pattern the functional elements.

11. (New) A method of manufacturing thin film elements, comprising:
 - transferring functional elements formed on a first substrate to a second substrate;
 - forming the functional elements in a predetermined shape on the first substrate via a peeling layer which causes peeling by application of a predetermined amount of energy; and
 - transferring at least one of the functional elements to the second substrate by applying the energy to relevant portions of the peeling layer corresponding to regions of the functional elements to cause peeling;
 - forming the functional elements in a predetermined shape including using dynamic auto focus system to pattern the functional elements.